BRIGHT LED ELECTRONICS CORP.

SINCE 1981

DATA SHEET

● DEVICE NUMBER：BL-BEG371J-T10-AA

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佰鴻工業股份有限公司

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APPROVED	DRAWER
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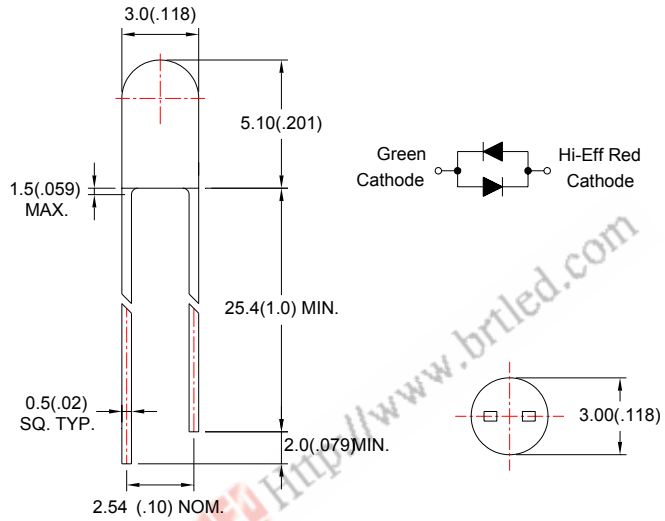
Features:

1. Chip material: GaAsP/GaP(Red) and GaP/GaP(Green)
2. Emitted color : Hi-Eff Red and Green
3. Lens Appearance : Water Clear
4. Low power consumption.
5. High efficiency.
6. Versatile mounting on P.C. Board or panel.
7. Low current requirement.
8. 3mm diameter package.
9. This product don't contained restriction substance, compliance ROHS standard.

Applications:

1. TV set
2. Monitor
3. Telephone
4. Computer
5. Circuit board

Package dimensions:



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is ±0.25mm (0.01") unless otherwise specified.
3. Lead spacing is measured where the leads emerge from the package.
4. Specifications are subject to change without notice.

Absolute Maximum Ratings(Ta=25℃)

Parameter	Symbol	Hi-Eff Red	Green	Unit
Power Dissipation	Pd	80	80	mW
Forward Current	I_F	30	30	mA
Peak Forward Current*[1]	I_{FP}	150	150	mA
Operating Temperature	Topr	-40℃~85℃		
Storage Temperature	Tstg	-40℃~100℃		
Soldering Temperature	Tsol	260℃max (for 5 seconds)		
Hand Soldering Temperature	Tsol	350℃max(for 3 seconds)		

*[1]Condition for I_{FP} is pulse of 1/10 duty and 0.1msec width.

● Electrical and optical characteristics(Ta=25℃)

Parameter	Symbol	Condition	Color	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F=10mA	Hi-Eff Red Green	- 	1.9 2.0	2.4 2.4	V
Luminous Intensity	Iv	I_F=10mA	Hi-Eff Red Green	-	10 12	-	mcd
Peak Wave Length	λp	I_F=10mA	Hi-Eff Red Green	-	640 568	-	nm
Dominant Wave Length	λd	I_F=10mA	Hi-Eff Red Green	617 560	-	638 576	nm
Spectral Line Half-width	Δλ	I_F=10mA	Hi-Eff Red Green	-	35 30	-	nm
Viewing Angle	$2\theta_{1/2}$	I_F=10mA	Hi-Eff Red Green	-	30	-	deg

● Typical Electro-Optical Characteristics Curves

Fig.1 Relative intensity vs. Wavelength

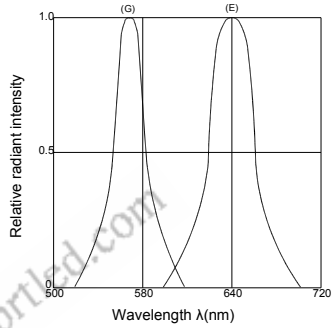


Fig.2 Forward current derating curve vs. Ambient temperature

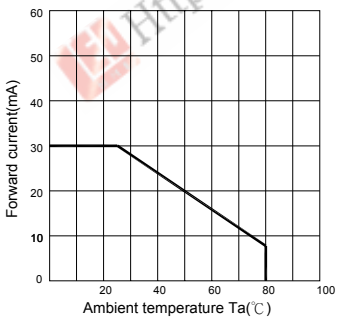


Fig.3 Forward current vs. Forward voltage

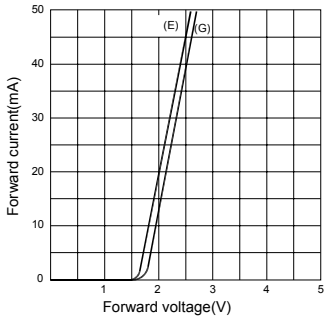


Fig.4 Relative luminous intensity vs. Ambient temperature

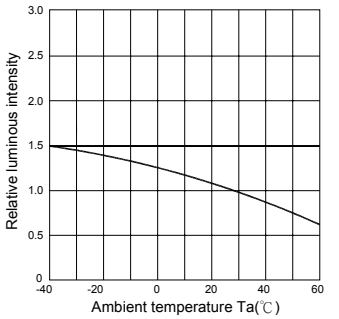


Fig.5 Relative luminous intensity vs. Forward current

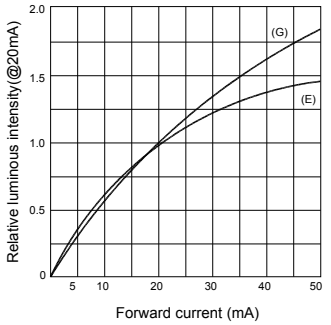
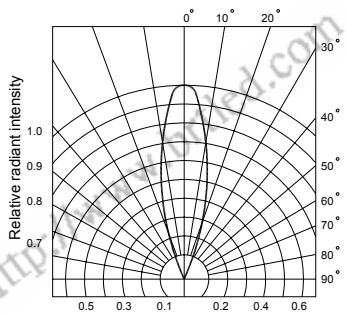


Fig.6 Radiation diagram



● Bin Limits(Green)

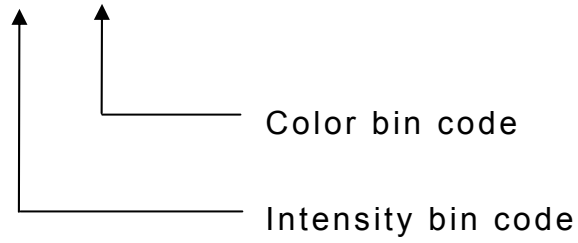
18. Intensity bin limits (At I_F= 10mA)

Bin Code	Min. (mcd)	Max. (mcd)
G	3.7	5.5
H	5.5	8.2
J	8.2	12.3
K	12.3	18.5
L	18.5	28

2. Color Bin Limits (At I_F=10mA) : Dominant Wave Length λd(nm)

Bin Code	Min. (nm)	Max. (nm)
1	560	562
2	562	564
3	564	566
4	566	568
5	568	570
6	570	572
7	572	574
8	574	576

● Bin : x x



NOTES:1.Tolerance of measurement of luminous intensity. :±15%

2.Tolerance of measurement of dominant wavelength :±1.0nm

● DIP soldering (Wave Soldering)

Preheating : 120℃,within 120~180 sec.
Operation heating : 255℃±5℃ within 5 sec.260℃ (Max)
Gradual Cooling (Avoid quenching).